



### Features

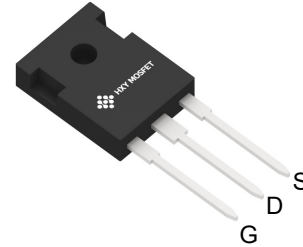
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Resistant to Latch-Up
- Halogen Free, RoHS Compliant

### Benefits

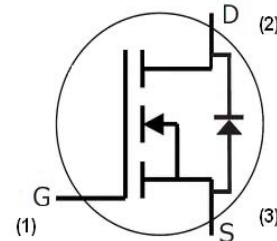
- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

### Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications



TO-247



Part Number	Package	Brand
HXYS36N120MP	TO-247	HXY MOSFET

### Maximum Ratings (T<sub>c</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>DSmax</sub>	Drain - Source Voltage	1200	V	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 100 μA	
V <sub>GSmax</sub>	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
V <sub>GSop</sub>	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I <sub>D</sub>	Continuous Drain Current	36	A	V <sub>GS</sub> = 20 V, T <sub>C</sub> = 25 °C	Fig. 19
		24		V <sub>GS</sub> = 20 V, T <sub>C</sub> = 100 °C	
I <sub>D(pulse)</sub>	Pulsed Drain Current	80	A	Pulse width t <sub>p</sub> limited by T <sub>Jmax</sub>	Fig. 22
P <sub>D</sub>	Power Dissipation	192	W	T <sub>c</sub> =25°C, T <sub>J</sub> = 150 °C	Fig. 20
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to +150	°C		
T <sub>L</sub>	Solder Temperature	260	°C	1.6mm (0.063") from case for 10s	
M <sub>d</sub>	Mounting Torque	1 8.8	Nm lbf-in	M3 or 6-32 screw	



**Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.9	4	V	$V_{DS} = V_{GS}, I_D = 5\ \text{mA}$	Fig. 11
			2.4		V	$V_{DS} = V_{GS}, I_D = 5\ \text{mA}, T_J = 150^\circ\text{C}$	
$I_{DSS}$	Zero Gate Voltage Drain Current		1	100	$\mu\text{A}$	$V_{DS} = 1200\ \text{V}, V_{GS} = 0\ \text{V}$	
$I_{GSS}$	Gate-Source Leakage Current			250	nA	$V_{GS} = 20\ \text{V}, V_{DS} = 0\ \text{V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		80	98	m $\Omega$	$V_{GS} = 20\ \text{V}, I_D = 20\ \text{A}$	Fig. 4, 5, 6
			144			$V_{GS} = 20\ \text{V}, I_D = 20\ \text{A}, T_J = 150^\circ\text{C}$	
$g_{fs}$	Transconductance		10		S	$V_{DS} = 20\ \text{V}, I_{DS} = 20\ \text{A}$	Fig. 7
			9			$V_{DS} = 20\ \text{V}, I_{DS} = 20\ \text{A}, T_J = 150^\circ\text{C}$	
$C_{iss}$	Input Capacitance		1130		pF	$V_{GS} = 0\ \text{V}$ $V_{DS} = 1000\ \text{V}$ $f = 1\ \text{MHz}$ $V_{AC} = 25\ \text{mV}$	Fig. 17, 18
$C_{oss}$	Output Capacitance		92				
$C_{riss}$	Reverse Transfer Capacitance		7.5				
$E_{oss}$	$C_{oss}$ Stored Energy		50				Fig. 16
$E_{AS}$	Avalanche Energy, Single Pluse		1		J	$I_D = 20\ \text{A}, V_{DD} = 50\ \text{V}$	Fig. 29
$E_{ON}$	Turn-On Switching Energy		523		$\mu\text{J}$	$V_{DS} = 800\ \text{V}, V_{GS} = -5/20\ \text{V}, I_D = 20\ \text{A}, R_{G(ext)} = 2.5\ \Omega, L = 156\ \mu\text{H}$	Fig. 25
$E_{OFF}$	Turn Off Switching Energy		72				
$t_{d(on)}$	Turn-On Delay Time		15		ns	$V_{DD} = 800\ \text{V}, V_{GS} = -5/20\ \text{V}$ $I_D = 20\ \text{A}, R_{G(ext)} = 2.5\ \Omega,$ $R_L = 40\ \Omega,$ Timing relative to $V_{DS}$ Per IEC60747-8-4 pg 83	Fig. 27
$t_r$	Rise Time		22				
$t_{d(off)}$	Turn-Off Delay Time		24				
$t_f$	Fall Time		14				
$R_{G(int)}$	Internal Gate Resistance		3.9		$\Omega$	$f = 1\ \text{MHz}, V_{AC} = 25\ \text{mV}$	
$Q_{gs}$	Gate to Source Charge		17		nC	$V_{DS} = 800\ \text{V}, V_{GS} = -5/20\ \text{V}$ $I_D = 20\ \text{A}$ Per IEC60747-8-4 pg 21	Fig. 12
$Q_{gd}$	Gate to Drain Charge		29				
$Q_g$	Total Gate Charge		71				

**Reverse Diode Characteristics**

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_{SD}$	Diode Forward Voltage	4.3		V	$V_{GS} = -5\ \text{V}, I_{SD} = 10\ \text{A}$	Fig. 8, 9, 10
		3.8		V	$V_{GS} = -5\ \text{V}, I_{SD} = 10\ \text{A}, T_J = 150^\circ\text{C}$	
$I_S$	Continuous Diode Forward Current		36	A	$T_C = 25^\circ\text{C}$	Note 1
$t_{rr}$	Reverse Recover time	24		ns	$V_{GS} = -5\ \text{V}, I_{SD} = 20\ \text{A}, V_R = 800\ \text{V}$ $dif/dt = 1950\ \text{A}/\mu\text{s}$	Note 1
$Q_{rr}$	Reverse Recovery Charge	152		nC		
$I_{rrm}$	Peak Reverse Recovery Current	10		A		

Note (1): When using SiC Body Diode the maximum recommended  $V_{GS} = -5\text{V}$

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.60	0.65	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient		40			



### Typical Performance

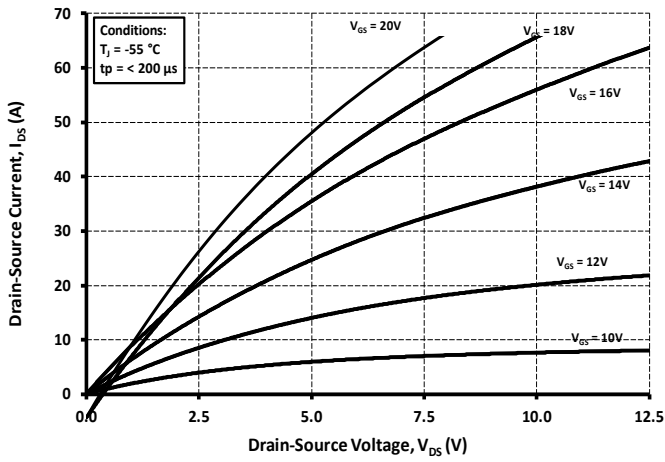


Figure 1. Output Characteristics  $T_J = -55\text{ }^\circ\text{C}$

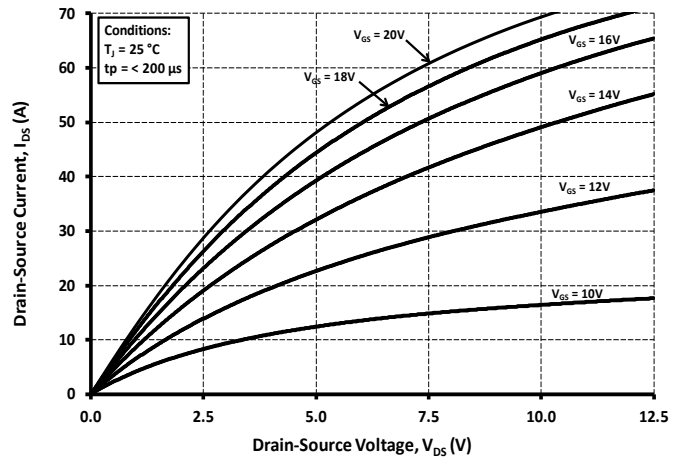


Figure 2. Output Characteristics  $T_J = 25\text{ }^\circ\text{C}$

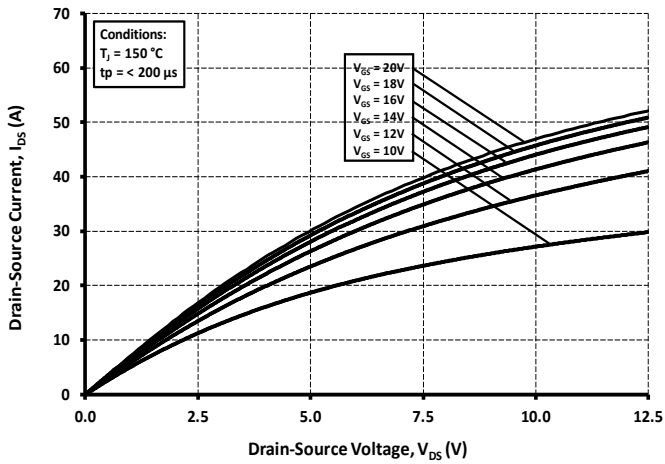


Figure 3. Output Characteristics  $T_J = 150\text{ }^\circ\text{C}$

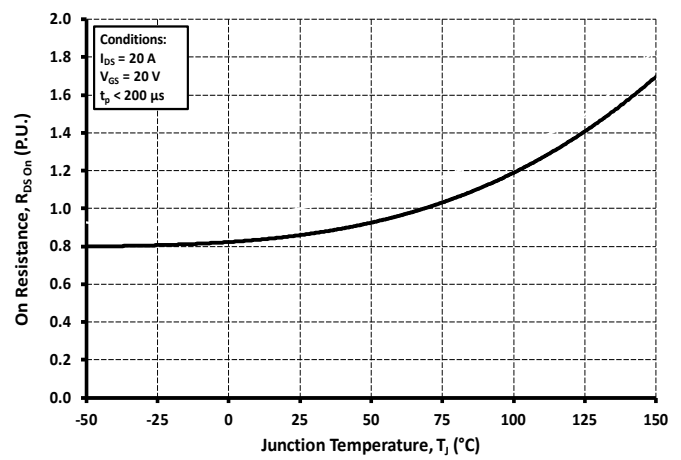


Figure 4. Normalized On-Resistance vs. Temperature

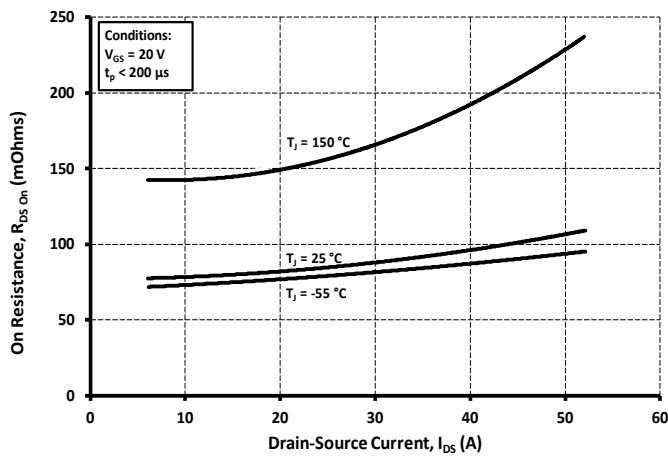


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

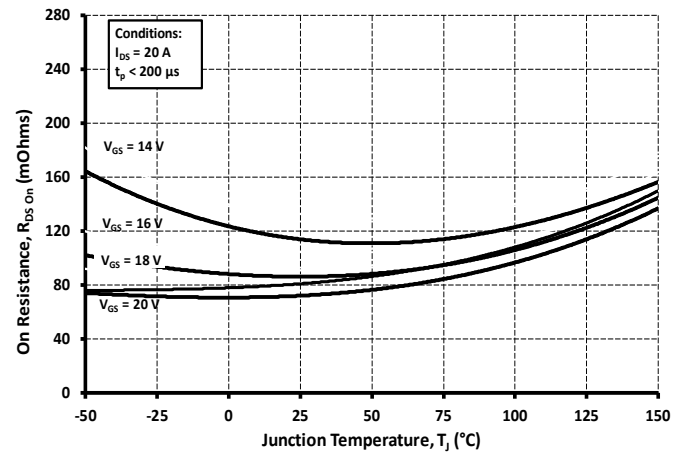


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

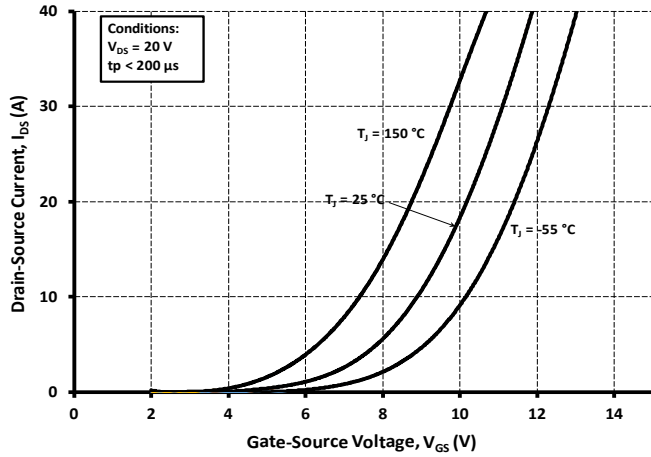


Figure 7. Transfer Characteristic for Various Junction Temperatures

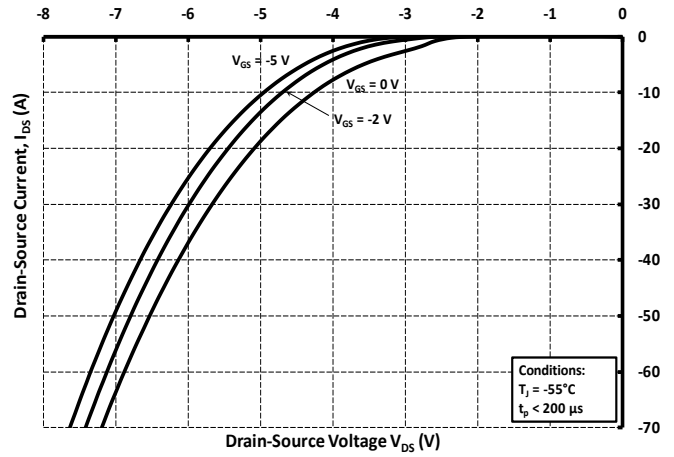


Figure 8. Body Diode Characteristic at -55 °C

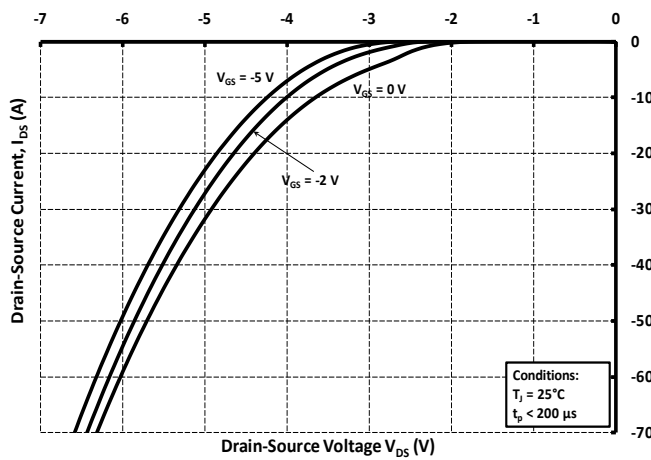


Figure 9. Body Diode Characteristic at 25 °C

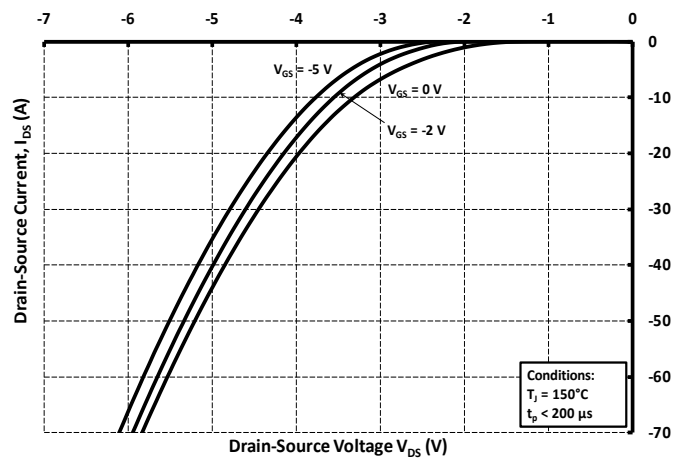


Figure 10. Body Diode Characteristic at 150 °C

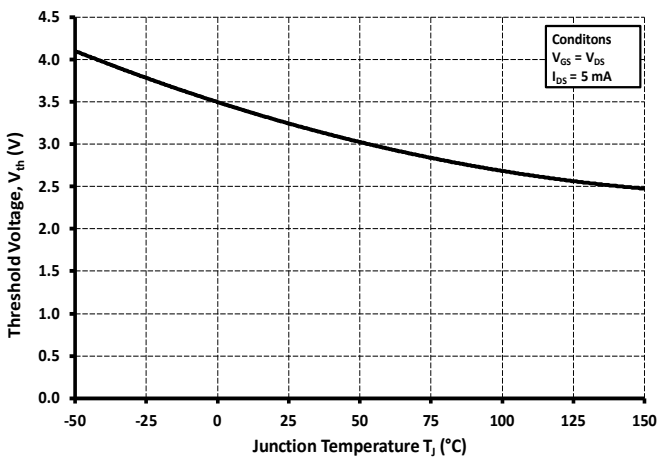


Figure 11. Threshold Voltage vs. Temperature

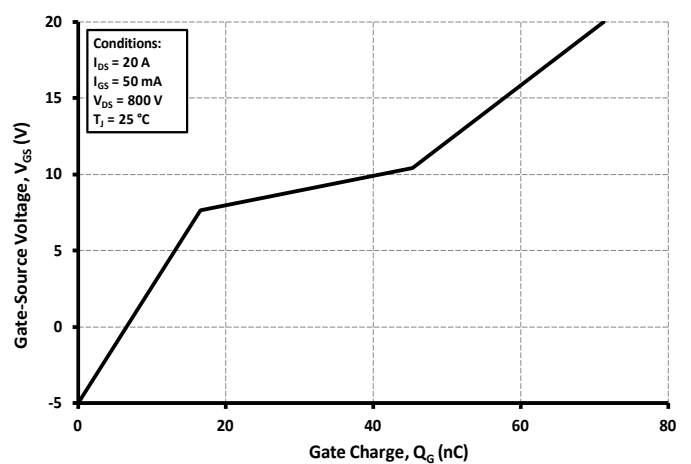


Figure 12. Gate Charge Characteristics

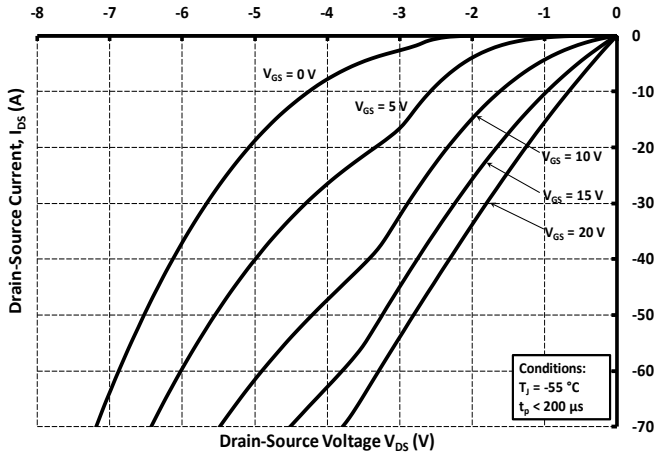


Figure 13. 3rd Quadrant Characteristic at -55 °C

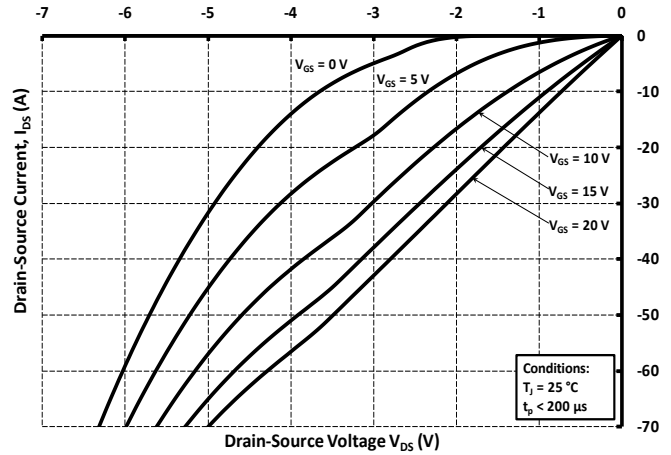


Figure 14. 3rd Quadrant Characteristic at 25 °C

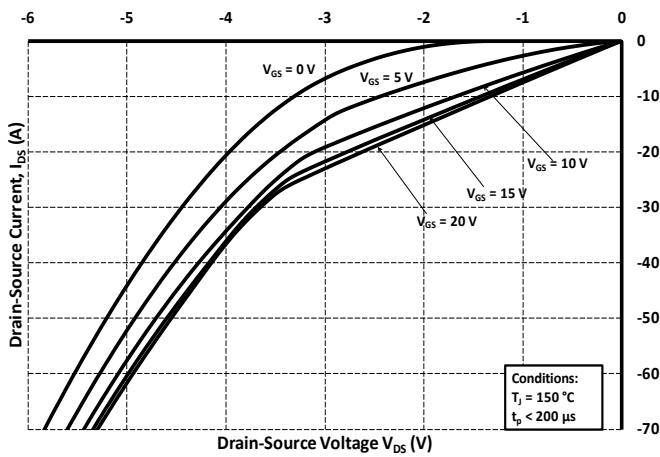


Figure 15. 3rd Quadrant Characteristic at 150 °C

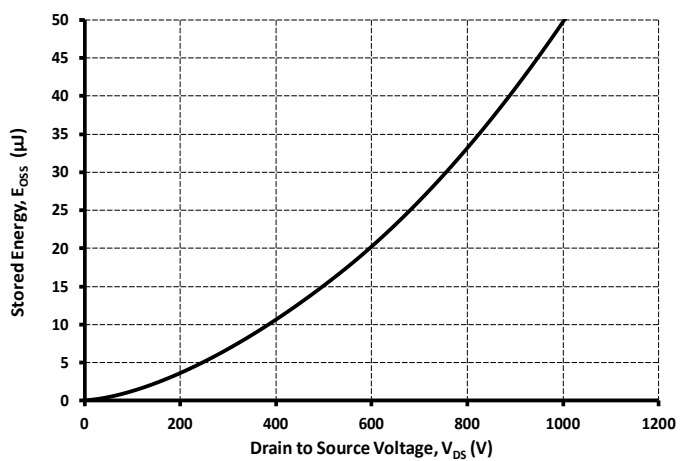


Figure 16. Output Capacitor Stored Energy

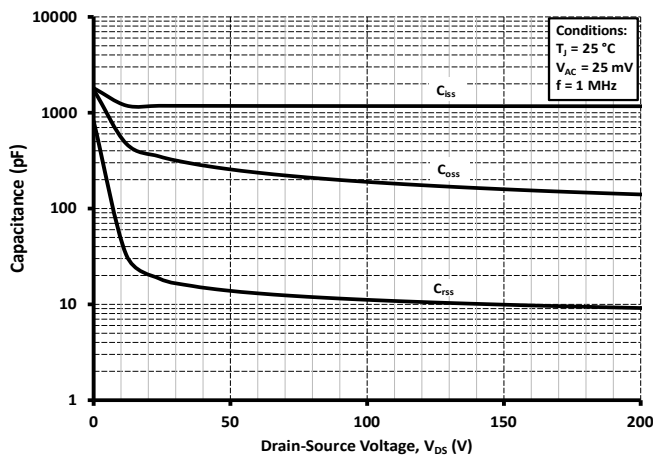


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

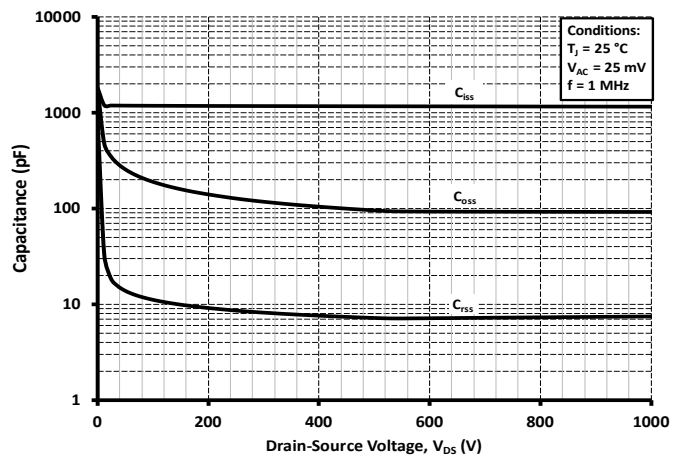


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

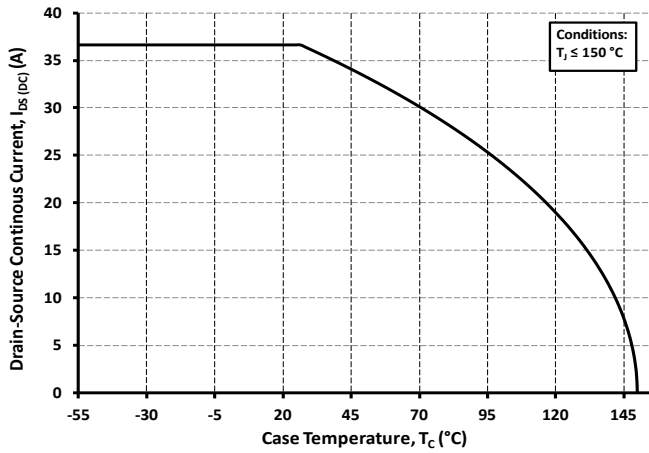


Figure 19. Continuous Drain Current Derating vs. Case Temperature

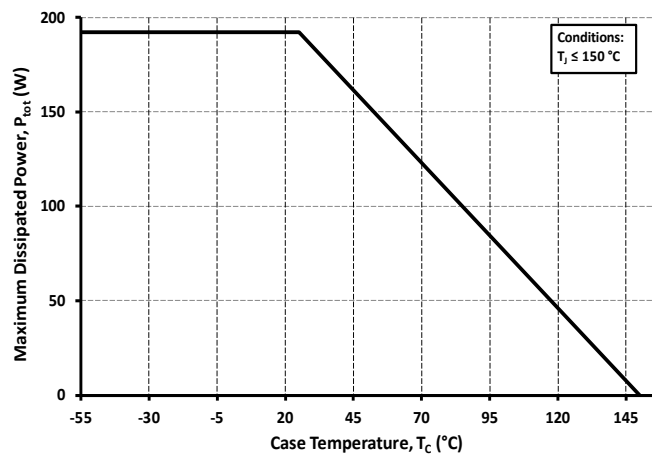


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

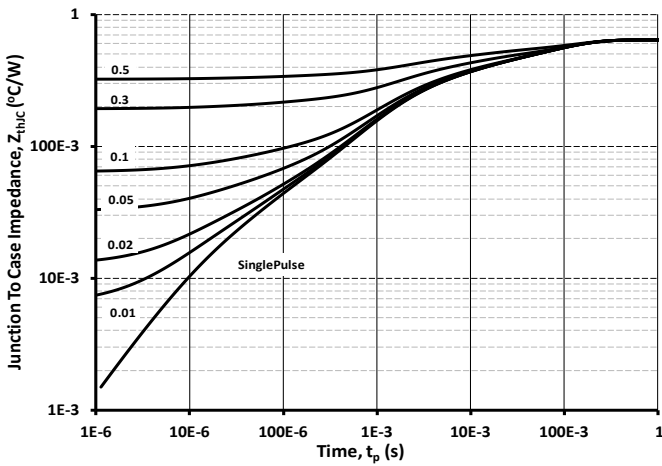


Figure 21. Transient Thermal Impedance (Junction - Case)

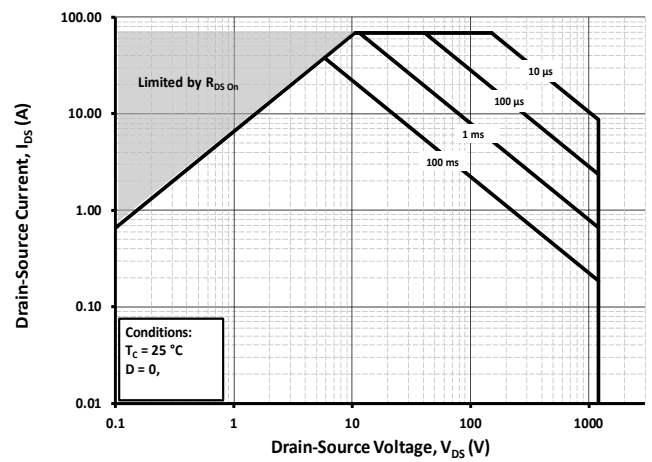


Figure 22. Safe Operating Area

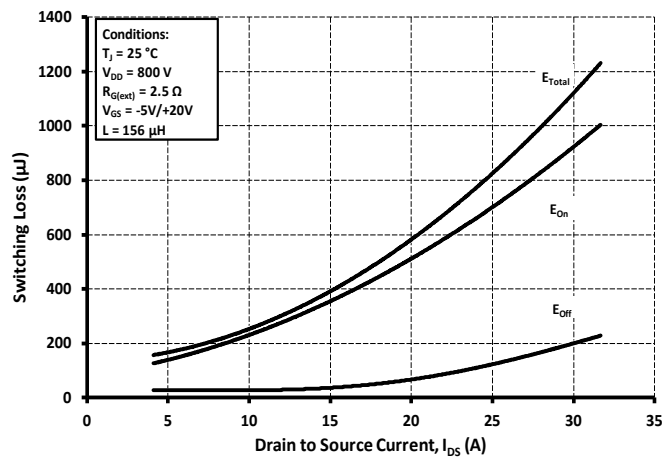


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 800V$ )

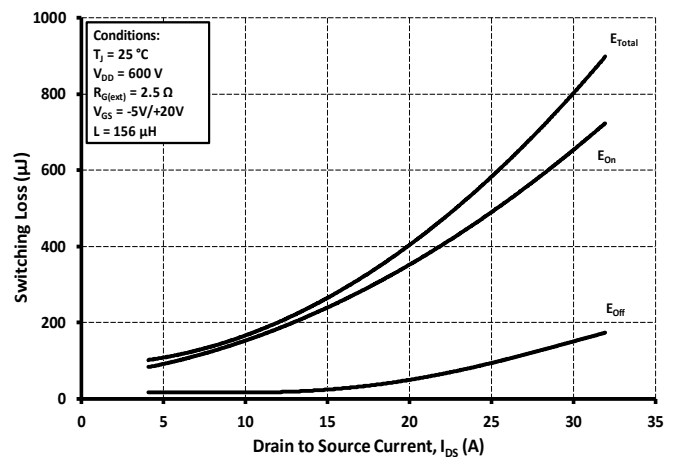


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 600V$ )

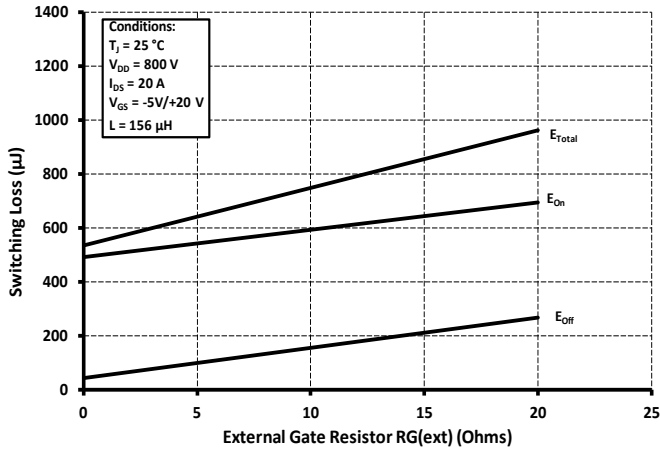


Figure 25. Clamped Inductive Switching Energy vs.  $R_{G(ext)}$

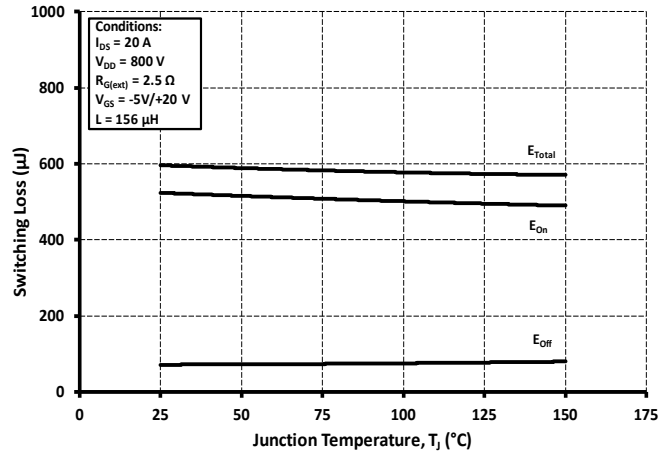


Figure 26. Clamped Inductive Switching Energy vs. Temperature

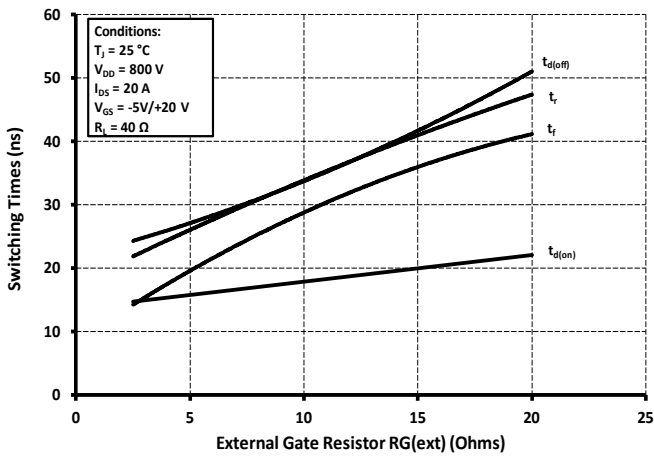


Figure 27. Switching Times vs.  $R_{G(ext)}$

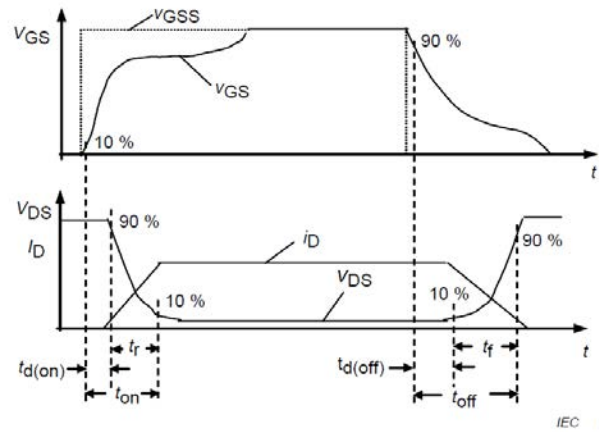


Figure 28. Switching Times Definition

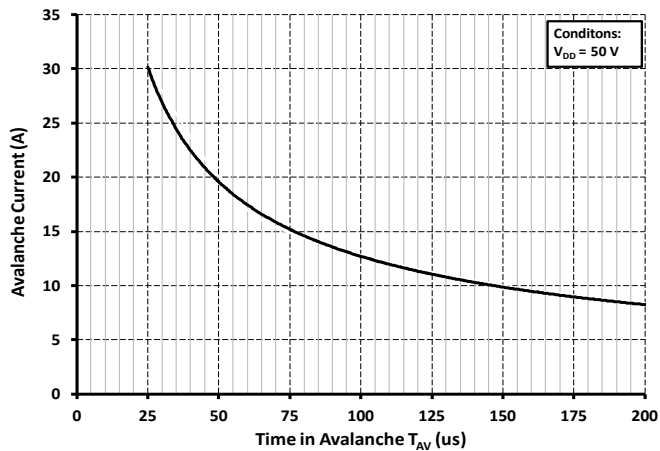


Figure 29. Single Avalanche SOA curve



### Test Circuit Schematic

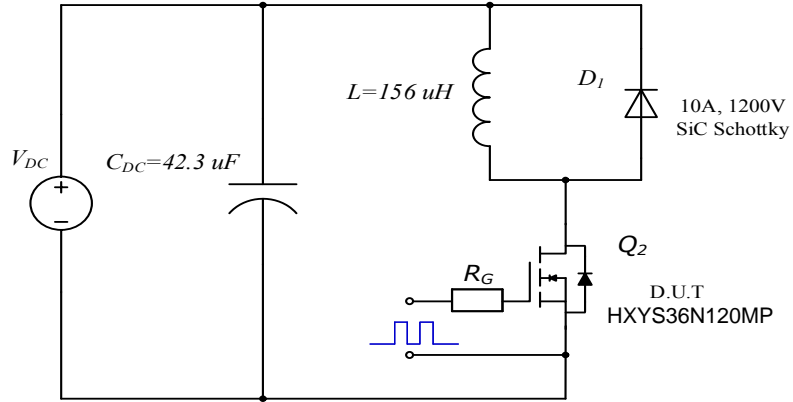


Figure 30. Clamped Inductive Switching Waveform Test Circuit

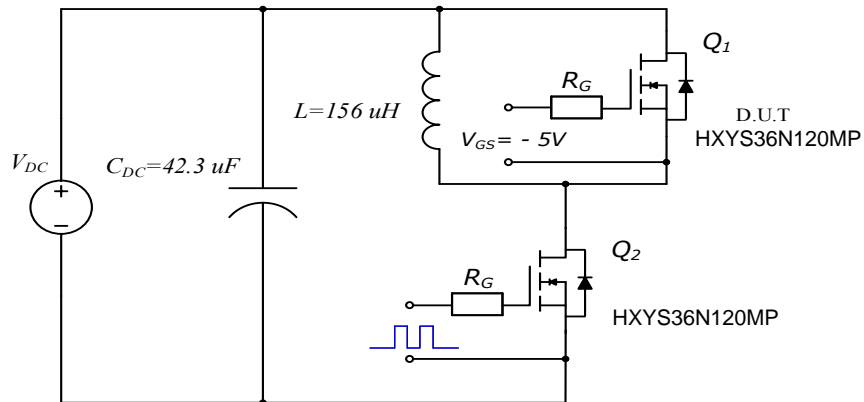


Figure 31. Body Diode Recovery Test Circuit

### ESD Ratings

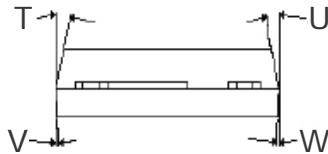
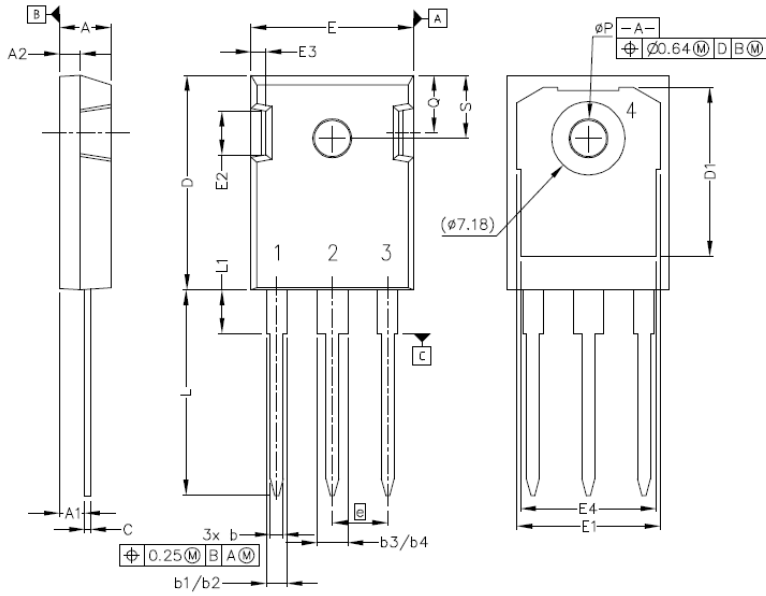
ESD Test	Total Devices Sampled	Resulting Classification
ESD-HBM	All Devices Passed 1000V	2 (>2000V)
ESD-MM	All Devices Passed 400V	C (>400V)
ESD-CDM	All Devices Passed 1000V	IV (>1000V)





### Package Dimensions

#### Package TO-247

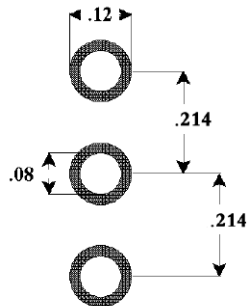


#### Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

#### Recommended Solder Pad Layout



TO247-3L



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